

The documentation and process conversion measures necessary to comply with this revision shall be completed by 31 January 2014.

INCH-POUND

MIL-PRF-19500/645D  
 31 October 2013  
 SUPERSEDING  
 MIL-PRF-19500/645C  
 24 August 2007

PERFORMANCE SPECIFICATION SHEET

SEMICONDUCTOR DEVICE, DIODE, SILICON, POWER RECTIFIER,  
 DUAL, COMMON CATHODE OR ANODE CENTER TAP, ULTRAFast,  
 TYPES 1N6772, 1N6773, 1N6772R AND 1N6773R  
 JAN, JANTX, JANTXV, AND JANS

This specification is approved for use by all Departments and Agencies of the Department of Defense.

The requirements for acquiring the product described herein shall consist of this specification sheet and MIL-PRF-19500.

1. SCOPE

1.1 This specification covers the performance requirements for silicon, dual ultrafast, power rectifier diodes in a center-tap configuration. Four levels of product assurance are provided for each device type as specified in MIL-PRF-19500.

1.2 Physical dimensions. See figure 1 (similar to TO-257AA, isolated).

1.3 Maximum ratings.

Types	$V_{RWM}$ (1) $I_D = 5 \mu A$ dc	$I_F$ (1) (2) $T_C = +100^\circ C$	$I_{FSM}$ (1) $t_p = 8.3$ ms	$R_{\theta JC}$ (1)	$R_{\theta JA}$ (1)	$T_{STG}$ and $T_J$
	Vdc	A dc	A (pk)	$^\circ C/W$	$^\circ C/W$	$^\circ C$
1N6772, 1N6772R	400	8.0	60	2.5	45	-65 to +150
1N6773, 1N6773R	600	8.0	60	2.5	45	-65 to +150

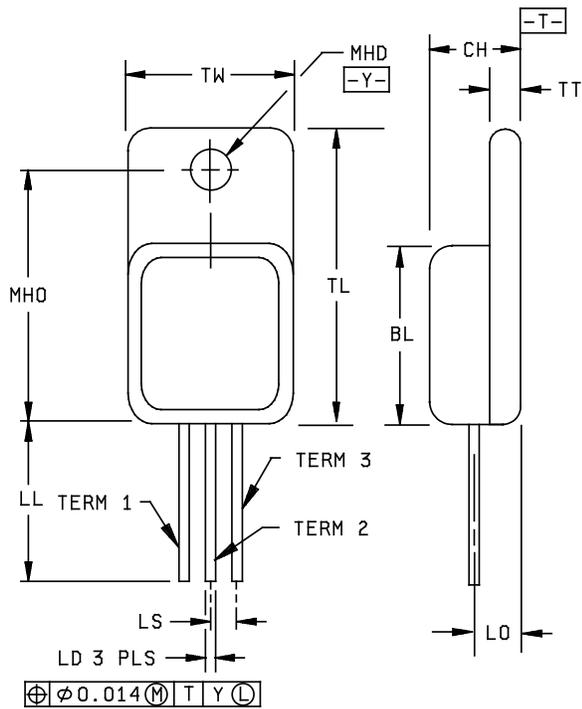
(1) Each individual diode.

(2) Derate at 160 mA/ $^\circ C$  above  $T_C = +100^\circ C$ .

1.4 Primary electrical characteristics. Unless otherwise specified, primary electrical characteristics are at +25 $^\circ C$ , and for each diode.

Types	$V_{F1}$ $I_F = 4$ A dc	$V_{F2}$ $I_F = 8$ A dc	$I_{R1}$ (see 1.3) $V_R = 0.8 V_{RWM}$	$I_{R2}$ $V_R = 0.8 V_{RWM}$ (see 1.3) $T_C = +100^\circ C$	$t_{rr}$	$C_J$ $V_R = 5$ V $f = 1$ MHz
	V dc	V dc	$\mu A$ dc	$\mu A$ dc	ns	pF
1N6772, 1N6772R	1.45	1.60	10	5000	60	200
1N6773, 1N6773R	1.45	1.60	10	5000	60	200

Comments, suggestions, or questions on this document should be addressed to Defense Supply Center, Columbus, ATTN: DSCC-VAC, P.O. Box 3990, Columbus, OH 43218-3990, or emailed to [Semiconductor@dsc.mil](mailto:Semiconductor@dsc.mil). Since contact information can change, you may want to verify the currency of this address information using the ASSIST Online database at <https://assist.dla.mil>.



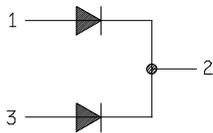
Symbol	Dimensions			
	Inches		Millimeters	
	Min	Max	Min	Max
BL	.410	.430	10.4	10.9
CH	.190	.200	4.82	5.08
LD	.025	.035	0.64	0.89
LL	.500	.750	12.70	19.05
LO	.120 typ		3.05 typ	
LS	.100 bsc		2.54 bsc	
MHD	.140	.150	3.55	3.80
MHO	.527	.537	13.4	13.6
TL	.645	.665	16.4	16.9
TT	.035	.045	0.90	1.15
TW	.410	.420	10.4	10.7

NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. All terminals are isolated from case.
4. In accordance with ASME Y14.5M, diameters are equivalent to  $\phi x$  symbology.

SCHEMATIC

1N6772, 1N6773



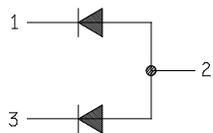
Terminal

Description

1  
2  
3

Anode 1  
Cathode  
Anode 2

1N6772R, 1N6773R



Terminal

Description

1  
2  
3

Cathode 1  
Anode  
Cathode 2

FIGURE 1. Physical dimensions and configuration (TO-257AA, isolated).

## 2. APPLICABLE DOCUMENTS

2.1 General. The documents listed in this section are specified in sections 3, 4, or 5 of this specification. This section does not include documents cited in other sections of this specification or recommended for additional information or as examples. While every effort has been made to ensure the completeness of this list, document users are cautioned that they must meet all specified requirements of documents cited in sections 3, 4, or 5 of this specification, whether or not they are listed.

### 2.2 Government documents.

2.2.1 Specifications, standards, and handbooks. The following specifications, standards, and handbooks form a part of this document to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

#### DEPARTMENT OF DEFENSE SPECIFICATIONS

MIL-PRF-19500 - Semiconductor Devices, General Specification for.

#### DEPARTMENT OF DEFENSE STANDARDS

MIL-STD-750 - Test Methods for Semiconductor Devices.

\* (Copies of these documents are available online at <http://quicksearch.dla.mil> or <https://assist.dla.mil>, or from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.3 Order of precedence. In the event of a conflict between the text of this document and the references cited herein, the text of this document takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

## 3. REQUIREMENTS

3.1 General. The individual item requirements shall be as specified in MIL-PRF-19500 and as modified herein.

3.2 Qualification. Devices furnished under this specification shall be products that are manufactured by a manufacturer authorized by the qualifying activity for listing on the applicable qualified manufacturer's list (QML) before contract award (see 4.2 and 6.3).

3.3 Abbreviations, symbols, and definitions. Abbreviations, symbols, and definitions used herein shall be as specified in MIL-PRF-19500.

3.4 Interface and physical dimensions. Interface and physical dimensions shall be as specified in MIL-PRF-19500, and on figure 1. When lead formation is performed, as a minimum, the vendor shall perform 100 percent hermetic seal in accordance with screen 14 of table II of MIL-PRF-19500 and 100 percent DC testing in accordance with group A, subgroup 2 herein.

3.4.1 Lead finish. Lead finish shall be solderable in accordance with MIL-PRF-19500, MIL-STD-750, and herein. Where a choice of lead finish is desired, it shall be specified in the acquisition document (see 6.2).

3.4.2 Polarity. Polarity and terminal configuration shall be in accordance with figure 1 herein.

3.5 Electrical performance characteristics. Unless otherwise specified herein, the electrical performance characteristics are as specified in 1.3, 1.4, and table I.

3.6 Electrical test requirements. The electrical test requirements shall be group A as specified herein.

3.7 Marking. Marking shall be in accordance with MIL-PRF-19500.

MIL-PRF-19500/645D

3.8 Workmanship. Semiconductor devices shall be processed in such a manner as to be uniform in quality and shall be free from other defects that will affect life, serviceability, or appearance.

4. VERIFICATION

4.1 Classification of inspections. The inspection requirements specified herein are classified as follows:

- a. Qualification inspection (see 4.2).
- b. Screening (see 4.3).
- c. Conformance inspection (see 4.4).

4.2 Qualification inspection. Qualification inspection shall be in accordance with MIL-PRF-19500 and as specified herein.

4.2.1 Group E qualification. Group E inspection shall be performed for qualification or re-qualification only. In case qualification was awarded to a prior revision of the specification sheet that did not request the performance of table II tests, the tests specified in table II herein that were not performed in the prior revision shall be performed on the first inspection lot of this revision to maintain qualification.

4.3 Screening (JANTX, JANTXV, and JANS levels). Screening shall be in accordance with appendix E, table E-IV of MIL-PRF-19500, and as specified herein. The following measurements shall be made in accordance with table I herein. Devices that exceed the limits of table I herein shall not be acceptable.

Screen (see Appendix E, table E-IV of MIL-PRF-19500)	Measurement	
	JANS level	JANTX and JANTXV levels
(1) 3c	Thermal impedance (see 4.3.2)	Thermal impedance (see 4.3.2)
9 and 10	Not applicable	Not applicable
11	$I_{R1}$ and $V_{F1}$	$I_{R1}$ and $V_{F1}$
12	See 4.3.1, $t = 240$ hours	See 4.3.1, $t = 48$ hours
13	Subgroups 2 and 3 of table I herein; $V_{F1}$ and $I_{R1}$ ; $\Delta I_{R1} \leq 100$ percent of initial value or $\pm 2.5 \mu A$ , whichever is greater; $\Delta V_{F1} \leq \pm 100$ mV.	Subgroup 2 of table I herein; $V_{F1}$ and $I_{R1}$ ; $\Delta I_{R1} \leq 100$ percent of initial value or $\pm 2.5 \mu A$ whichever is greater; $\Delta V_{F1} \leq \pm 100$ mV.

\* (1) Thermal impedance shall be performed any time after temperature cycling, screen 3a, JANTX and JANTXV levels do not need to be repeated in screening requirements.

4.3.1 Power burn-in conditions. Power burn-in conditions are as follows: Method 1038 of MIL-STD-750, test condition A.  $T_C = +125^\circ C$ ;  $V_R = 0.8$  of rated  $V_{RWM}$  (see 1.3).

4.3.2 Thermal impedance The thermal impedance measurements shall be performed in accordance with method 3101 or 4081 of MIL-STD-750. The thermal impedance conditions and maximum thermal impedance limit shall be derived by each vendor. The chosen thermal impedance measurement and conditions for each device in the qualification lot shall be submitted in the qualification report and a thermal impedance curve shall be plotted (see table II, subgroup 4 herein).

MIL-PRF-19500/645D

4.4 Conformance inspection. Conformance inspection shall be in accordance with MIL-PRF-19500 and as specified herein.

4.4.1 Group A inspection. Group A inspection shall be conducted in accordance with MIL-PRF-19500 and table I, subgroup 2 herein. Electrical measurements (end-points) and delta requirements shall be in accordance with the applicable steps of table III herein.

4.4.2 Group B inspection. Group B inspection shall be conducted in accordance with the conditions specified for subgroup testing in appendix E, table E-VIa (JANS) and table E-VIb (JANTX and JANTXV) of MIL-PRF-19500 and as follows. Electrical measurements (end-points) and delta requirements shall be in accordance with the applicable steps of table III herein.

4.4.2.1 Group B inspection, appendix E, table E-VIa (JANS) of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
B4	1037	$I_F$ or $I_O = 1.25$ A to 8 A; $\Delta T_J = +85^\circ\text{C}$ minimum.

4.4.2.2 Group B inspection, appendix E, table E-VIb (JANTX and JANTXV) of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
B3	1037	$I_F$ or $I_O = 1.25$ A to 8 A; $\Delta T_J = +85^\circ\text{C}$ minimum, for 2,000 cycles minimum.
B5		Not applicable.

4.4.3 Group C inspection. Group C inspection shall be conducted in accordance with the conditions specified for subgroup testing in appendix E, table E-VII of MIL-PRF-19500 and as follows. Electrical measurements (end-points) and delta requirements shall be in accordance with the applicable steps of table III herein.

4.4.3.1 Group C inspection, appendix E, table E-VII of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
C2	2036	Test condition A, 5 pounds, $t = 15$ seconds $\pm 3$ seconds.
C5	4081	$R_{\theta JC}$ (maximum) = $2.5$ $^\circ\text{C}/\text{W}$ .
C6	1037	$I_F$ or $I_O = 1.25$ A to 10 A; $\Delta T_J = +85^\circ\text{C}$ minimum, for 6,000 cycles minimum.

4.4.4 Group E inspection. Group E inspection shall be conducted in accordance with the conditions specified for subgroup testing in table II herein. Electrical measurements (end-points) and delta requirements shall be in accordance with the applicable steps and footnotes of table III herein.

4.5 Methods of inspection. Methods of inspection shall be as specified in the appropriate tables and as follows.

4.5.1 Pulse measurements. Conditions for pulse measurement shall be as specified in section 4 of MIL-STD-750.

## MIL-PRF-19500/645D

TABLE I. Group A inspection. 1/ 2/

Inspection	MIL-STD-750		Symbol	Limits		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 1</u>						
Visual and mechanical examination	2071					
<u>Subgroup 2</u>						
Thermal impedance	3101	See 4.3.2	$Z_{\theta JX}$			°C/W
Breakdown voltage 1N6772, 1N6772R 1N6773, 1N6773R	4022	$I_R = 5 \mu\text{A dc}$ , pulsed <u>3/</u>	$V_{BR}$	400 600		V dc
Forward voltage	4011	$I_F = 4 \text{ A dc}$ , pulsed <u>3/</u> $I_F = 8 \text{ A dc}$ , pulsed <u>3/</u>	$V_{F1}$ $V_{F2}$		1.45 1.60	V dc V dc
Reverse leakage current	4016	DC method; pulsed <u>3/</u> $V_R = 0.8$ of $V_{RWM}$ (see 1.3)	$I_{R1}$		10	$\mu\text{A dc}$
<u>Subgroup 3</u>						
High temperature operation:		$T_C = +100^\circ\text{C}$				
Reverse leakage Current	4016	DC method; pulsed <u>3/</u> $V_R = 0.8$ of $V_{RWM}$ (see 1.3)	$I_{R2}$		500	$\mu\text{A dc}$
Low temperature operation:		$T_A = -55^\circ\text{C}$				
Forward voltage	4011	$I_F = 8 \text{ A dc}$ , pulsed <u>3/</u>	$V_{F3}$		1.80	V dc
<u>Subgroup 4</u>						
Scope display evaluation <u>4/</u>	4023					
Reverse recovery time measurements	4031	Condition B1	$t_{rr}$		60	ns

See footnotes at end of table.

TABLE I. Group A inspection – Continued. 1/ 2/

Inspection	MIL-STD-750		Symbol	Limits		Unit
	Method	Conditions		Min	Max	
<u>Subgroups 5 and 6</u> Not applicable						
<u>Subgroup 7</u> Junction capacitance	4001	$V_R = 5 \text{ V dc}; f = 1.0 \text{ MHz}$	$C_J$		200	pF

1/ For sampling plan, see MIL-PRF-19500.

2/ Each individual diode.

3/ Pulse test: Pulse width = 300  $\mu\text{s}$ , duty cycle  $\leq 2$  percent.

\* 4/ The reverse breakdown characteristics shall be viewed on an oscilloscope with display calibration factors of 2 to 5  $\mu\text{A/division}$  and 50 to 100  $\text{V/division}$ . Reverse current over the knee shall be at least 20 - 50  $\mu\text{A}$ . Each device may exhibit a slightly rounded characteristic and any discontinuity or dynamic instability of the trace shall be cause for rejection.

MIL-PRF-19500/645D

\* TABLE II. Group E inspection (all quality levels) for qualification and requalification only.

Inspection	MIL-STD-750		Sampling plan
	Method	Conditions	
* <u>Subgroup 1</u>			45 devices c = 0
Temperature cycling	1051	500 cycles	
Hermetic seal	1071		
Fine leak			
Gross leak			
Electrical measurements		See table III herein, steps 1, 2, 3, 4, 5, and 6.	
<u>Subgroup 2</u>			22 devices c = 0
Steady-state reverse bias	1038	Test condition A t = 1,000 hours, T <sub>C</sub> = +125°C V <sub>R</sub> = 0.8 of rated V <sub>RWM</sub> (see 1.3)	
Electrical measurements		See table III herein, steps 1, 2, and 6.	
<u>Subgroup 4</u>			
Thermal impedance curves		See MIL-PRF-19500.	
<u>Subgroup 5</u>			15 devices c = 0
Barometric pressure (reduced)	1001	V <sub>R</sub> = rated V <sub>RWM</sub> (see 1.3)	
* <u>Subgroup 8</u>			11 devices c = 0
Peak reverse power	4065	Peak reverse power (P <sub>RM</sub> ) = shall be characterized by the supplier and the data shall be available to the Government. Test shall be performed on each subplot.	
Electrical measurement		During the P <sub>RM</sub> test, the voltage (V <sub>BR</sub> ) shall be monitored to verify it has not collapsed. Any collapse in V <sub>BR</sub> during or after the P <sub>RM</sub> test or rise in leakage current (I <sub>R</sub> ) after the test that exceeds I <sub>R1</sub> in <a href="#">table I</a> , herein shall be considered a failure to that level of applied P <sub>RM</sub> . Progressively higher levels of P <sub>RM</sub> shall be applied until failure occurs on all devices within the chosen sample size.	
<u>Subgroup 10</u>			22 devices c = 0
Forward surge	4066	I <sub>FSM</sub> = rated (see col. 5 of <a href="#">1.3.2</a> ); ten surges of 8.3 ms each at 1 minute intervals superimposed on I <sub>O</sub> = 1.0 A (see col. 2 of <a href="#">1.3.2</a> ); V <sub>RWM</sub> = rated (see col. 4 of <a href="#">1.3.2</a> ); T <sub>A</sub> = + 55°C.	
Electrical measurement		See table I, subgroup 2 and table III, steps 1 and 2, herein.	

MIL-PRF-19500/645D

TABLE III. Groups A, B, C, and E electrical and delta measurements. 1/ 2/ 3/ 4/

Step	Inspection	MIL-STD-750		Symbol	Limits		Unit
		Method	Conditions		Min	Max	
1	Forward voltage	4011	$I_F = 8$ A dc pulsed	$V_{F2}$		1.60	V dc
2	Reverse leakage current	4016	$V_R = 0.8$ of percent $V_{RWM}$ (see 1.3) DC method, pulsed	$I_{R1}$		10	$\mu$ A dc
3	Forward voltage	4011	$I_F = 8$ A dc pulsed	$\Delta V_{F2}$		$\pm 100$ mV dc from initial reading	
4	Reverse leakage current	4016	$V_R = 0.8$ of percent $V_{RWM}$ (see 1.3) DC method, pulsed	$\Delta I_{R1}$		100 percent of initial value or $\pm 2.5$ $\mu$ A dc whichever is greater.	
5	Thermal impedance	3101	See 4.3.2	$Z_{\theta JX}$		2.3	$^{\circ}$ C/W
6 5/	Reverse recovery time	4031	See table I, subgroup 4 herein.	$t_{rr}$		60	ns

1/ The electrical measurements for table E-VIa (JANS) of MIL-PRF-19500 are as follows:

- a. Subgroup 3, see table III herein, steps 1 and 2.
- b. Subgroup 4, see table III herein, steps 1, 2, 3, 4, 5, and 6.
- c. Subgroup 5, see table III herein, steps 1, 2, 3, 4, and 6.

2/ The electrical measurements for table E-VIb (JANTX and JANTXV) of MIL-PRF-19500 are as follows:

- a. Subgroup 2, see table III herein, steps 1, 2, 5, and 6.
- b. Subgroup 3, see table III herein, steps 1, 2, 3, 4, 5, and 6.
- c. Subgroup 6, see table III herein, steps 1 and 2.

3/ The electrical measurements for table E-VII of MIL-PRF-19500 are as follows:

- a. Subgroup 2 see table III herein, steps 1, 2, and 5 for all levels.
- b. Subgroup 6, see table III herein, steps 1, 2, 3, 4, 5, and 6 for all levels.

4/ The electrical measurements for table E-IX of MIL-PRF-19500 are as follows:

- a. Subgroup 1, see table III herein, steps 1, 2, 3, 4, 5, and 6.
- b. Subgroup 2, see table III herein, steps 1 and 2.

5/ Step 6 applies to irradiated devices only.

## 5. PACKAGING

5.1 Packaging. For acquisition purposes, the packaging requirements shall be as specified in the contract or order (see 6.2). When packaging of materiel is to be performed by DoD or in-house contractor personnel, these personnel need to contact the responsible packaging activity to ascertain packaging requirements. Packaging requirements are maintained by the Inventory Control Point's packaging activities within the Military Service or Defense Agency, or within the Military Service's system commands. Packaging data retrieval is available from the managing Military Department's or Defense Agency's automated packaging files, CD-ROM products, or by contacting the responsible packaging activity.

## 6. NOTES

(This section contains information of a general or explanatory nature that may be helpful, but is not mandatory. The notes specified in MIL-PRF-19500 are applicable to this specification.)

6.1 Intended use. Semiconductors conforming to this specification are intended for original equipment design applications and logistic support of existing equipment.

6.2 Acquisition requirements. Acquisition documents should specify the following:

- a. Title, number, and date of this specification.
- b. Packaging requirements (see 5.1).
- c. Lead finish (see 3.4.1).
- d. Product assurance level and type designator.

\* 6.3 Qualification. With respect to products requiring qualification, awards will be made only for products which are, at the time of award of contract, qualified for inclusion in Qualified Manufacturers List (QML 19500) whether or not such products have actually been so listed by that date. The attention of the contractors is called to these requirements, and manufacturers are urged to arrange to have the products that they propose to offer to the Federal Government tested for qualification in order that they may be eligible to be awarded contracts or orders for the products covered by this specification. Information pertaining to qualification of products may be obtained from DLA Land and Maritime, ATTN: DSCC/VQE, P.O. Box 3990, Columbus, OH 43218-3990 or e-mail [yqe.chief@dla.mil](mailto:yqe.chief@dla.mil). An online listing of products qualified to this specification may be found in the Qualified Products Database (QPD) at <https://assist.dla.mil>.

6.4 Cross reference list. Parts covered by this specification may be used to replace the following commercial Part or Identifying Numbers (PIN):

Preferred types	Commercial types
JAN1N6772, JAN1N6772R JANTX1N6772, JANTX1N6772R JANTXV1N6772, JANTXV1N6772R JANS1N6772, JANS1N6772R	1N6772, 1N6772R
JAN1N6773, JAN1N6773R JANTX1N6773, JANTX1N6773R JANTXV1N6773, JANTXV1N6773R JANS1N6773, JANS1N6773R	1N6773, 1N6773R

MIL-PRF-19500/645D

6.4 Changes from previous issue. The margins of this specification are marked with asterisks to indicate where changes from the previous issue were made. This was done as a convenience only and the Government assumes no liability whatsoever for any inaccuracies in these notations. Bidders and contractors are cautioned to evaluate the requirements of this document based on the entire content irrespective of the marginal notations and relationship to the last previous issue.

Custodians  
Army - CR  
Navy - EC  
Air Force - 85  
NASA - NA  
DLA -CC

Preparing activity:  
DLA - CC  
  
(Project 5961-2013-067)

Air Force - 99

NOTE: The activities listed above were interested in this document as of the date of this document. Since organizations and responsibilities can change, you should verify the currency of the information above using the ASSIST Online database at <https://assist.dla.mil>.